

Lab Report III

Finding the resistivity using 4 probs

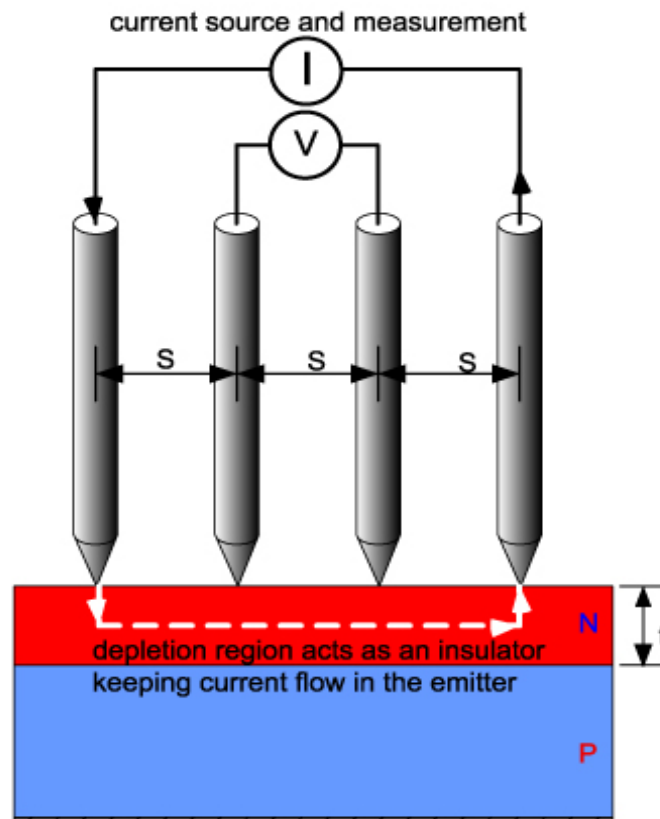
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Objective: Use probe4 resistivity and measure the sheet resistivity (ohm-cm) of a Si sample. By knowing the sheet resistance we can calculate the resistivity with multiplying the thinness of the sheet

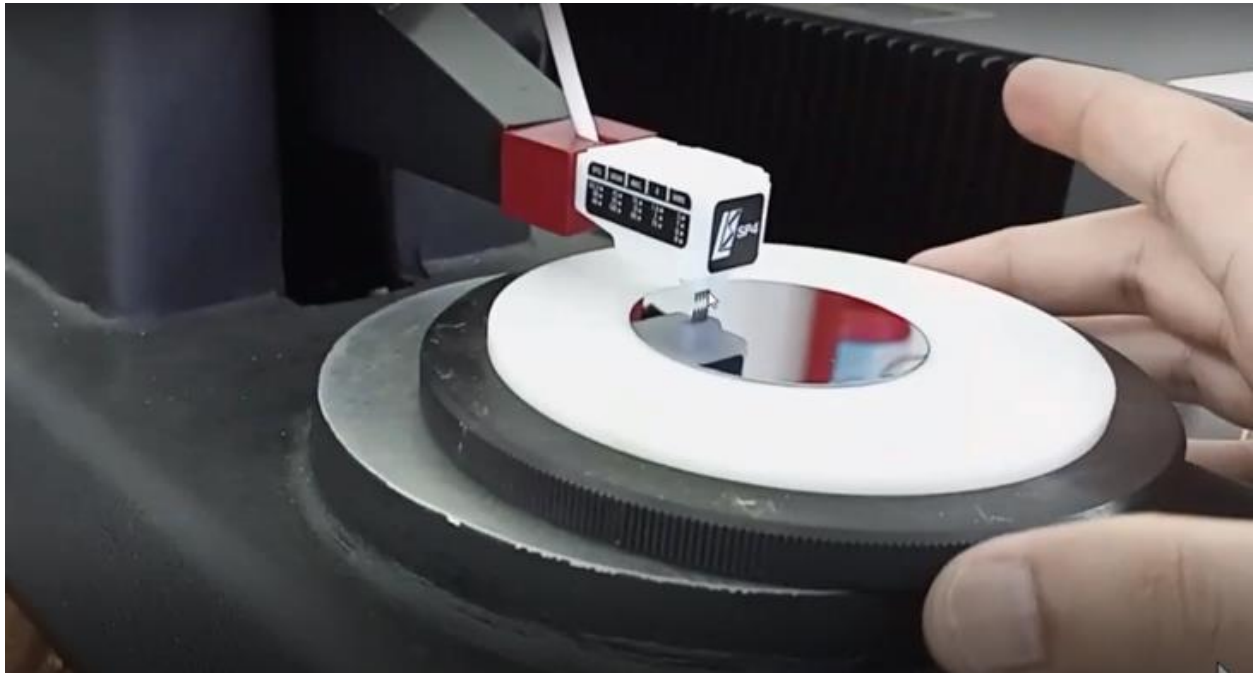
Theory :

The sheet resistivity of the top emitter layer is very easy to measure experimentally using a "four point probe". A current is passed through the outer probes and induces a voltage in the inner voltage probes. The junction between the n and p -type materials behaves as an insulating layer and the cell must be kept in the dark.



Procedure:

Let's take a p-type Si wafer which is having 2 inch diameter and thickness 500 micro meters.

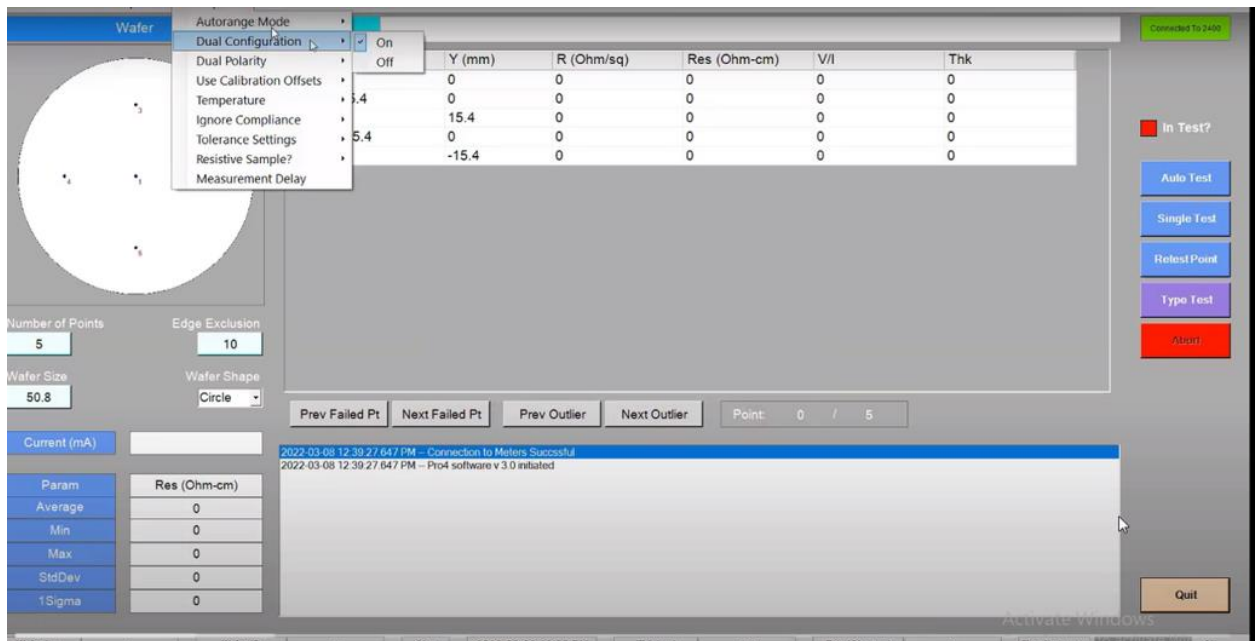


Signatone four probe resistivity meter has 4 probes and these probes are collinear, with the help of inner two probes we measure the current and remaining two use to measure voltage. Ratio of voltage and current gives the resistivity of the sample. Current in the inner probes flows in the order of mille or micro amps.

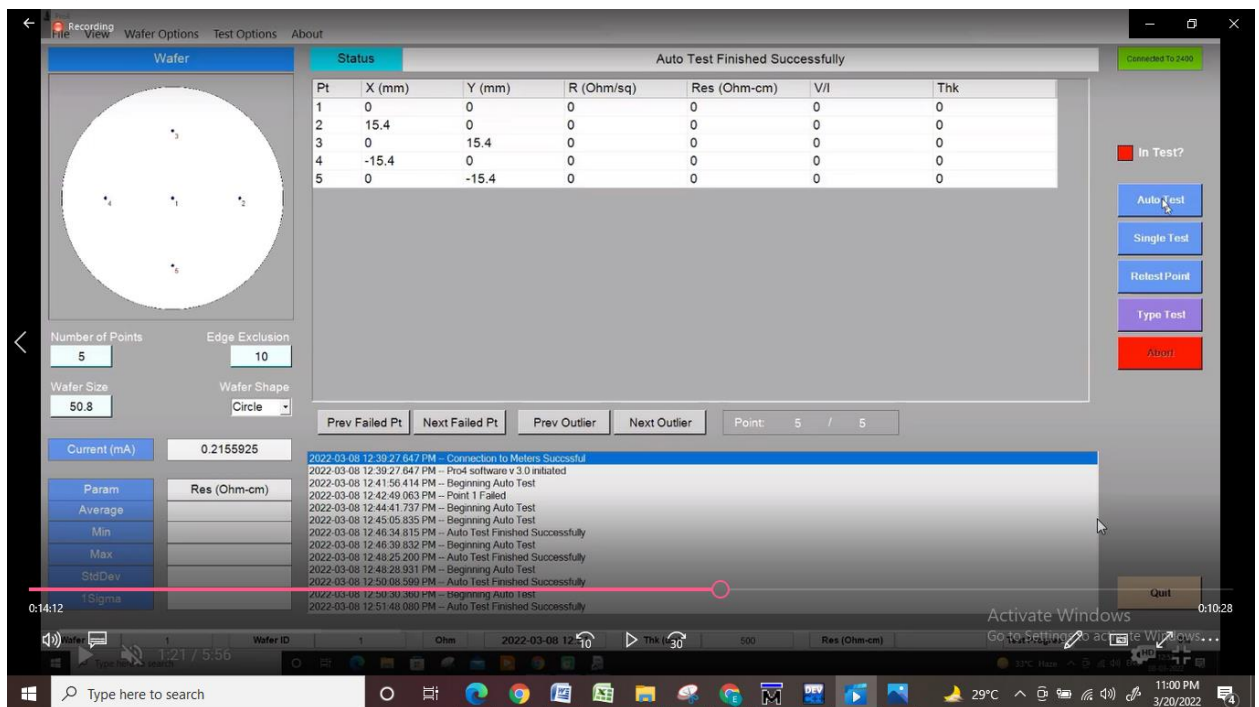
Following picture is 2410 Source meter which is used for probing current and voltage simultaneously. It can detect up to 1100 v.



- ➔ While taking the measurements these 4 probes have to be tight contact with si wafer surface.
- ➔ Software used here is probe4
Various options available in prob4 interface.



Auto range mode is selects range of currents from micro amps to mill amps, and measures voltages. We use NIST certified calibration, dual configuration is to choose the either positive or negative type of current. Complacence value is upper limit of the current or voltage to measure.



Single test:

The image displays two screenshots of the Pro4 software interface, showing the 'Single Test' process.

Top Screenshot: Auto Test Finished Successfully

The interface shows the 'Wafer' tab with a circular wafer diagram and five test points. The 'Status' tab displays the test results table:

Pt	X (mm)	Y (mm)	R (Ohm/sq)	Res (Ohm-cm)	V/I	Thk
1	0	0	0	0	0	0
2	15.4	0	0	0	0	0
3	0	15.4	0	0	0	0
4	-15.4	0	0	0	0	0
5	0	-15.4	0	0	0	0

The 'Pretest Check' dialog box is open, showing the following settings:

- Wafer ID: 1
- Wafer Lot: 1
- Known Constant: Thickness
- Thickness (um): 500
- Current (mA): Autorange

The 'Status' tab also shows a log of test events, including 'Connection to M...', 'Pro4 software v 3.0 initiated', 'Beginning Auto Test', 'Point 1 Failed', and 'Auto Test Finished Successfully'.

Bottom Screenshot: Doing Autorange

The interface shows the 'Wafer' tab with the same circular wafer diagram. The 'Status' tab displays the test results table, which is identical to the top screenshot.

A 'Post Message Screen' dialog box is open, displaying the message: 'Please move to desired point and lower probe head and press ok'. The 'OK' button is highlighted.

The 'Status' tab also shows a log of test events, including 'Connection to M...', 'Pro4 software v 3.0 initiated', 'Beginning Auto Test', 'Point 1 Failed', and 'Auto Test Finished Successfully'.



Single Test results:

Pt	X (mm)	Y (mm)	R (Ohm/sq)	Res (Ohm-cm)	V/I	Thk
1	0	0	91262.070313	4556.056641	20141.705078	500
2	15.4	0	0	0	0	0
3	0	15.4	0	0	0	0
4	-15.4	0	0	0	0	0
5	0	-15.4	0	0	0	0

Auto test:

Here we are performing 5 point measurements. So, each time have to move the point when following message displace.

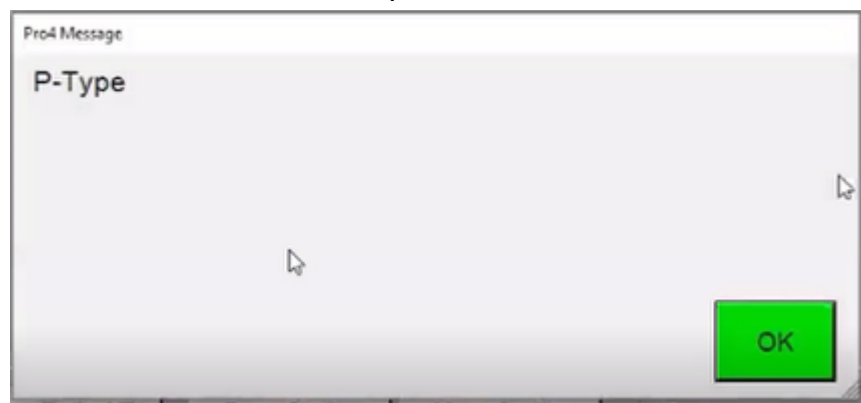


Test results for auto test:

Status		Auto Test Finished Successfully				
Pt	X (mm)	Y (mm)	R (Ohm/sq)	Res (Ohm-cm)	V/I	Thk
1	0	0	93184.6875	4652.039063	20566.03125	500
2	15.4	0	93820.101563	4683.760254	20706.267578	500
3	0	15.4	93962.726563	4690.880859	20737.746094	500
4	-15.4	0	94520.890625	4718.745605	20860.933594	500
5	0	-15.4	95096.820313	4747.498047	20988.041016	500

Type test:

Here we need to make sure that 4 probes contact with si wafer.



Verify with analytical expressions